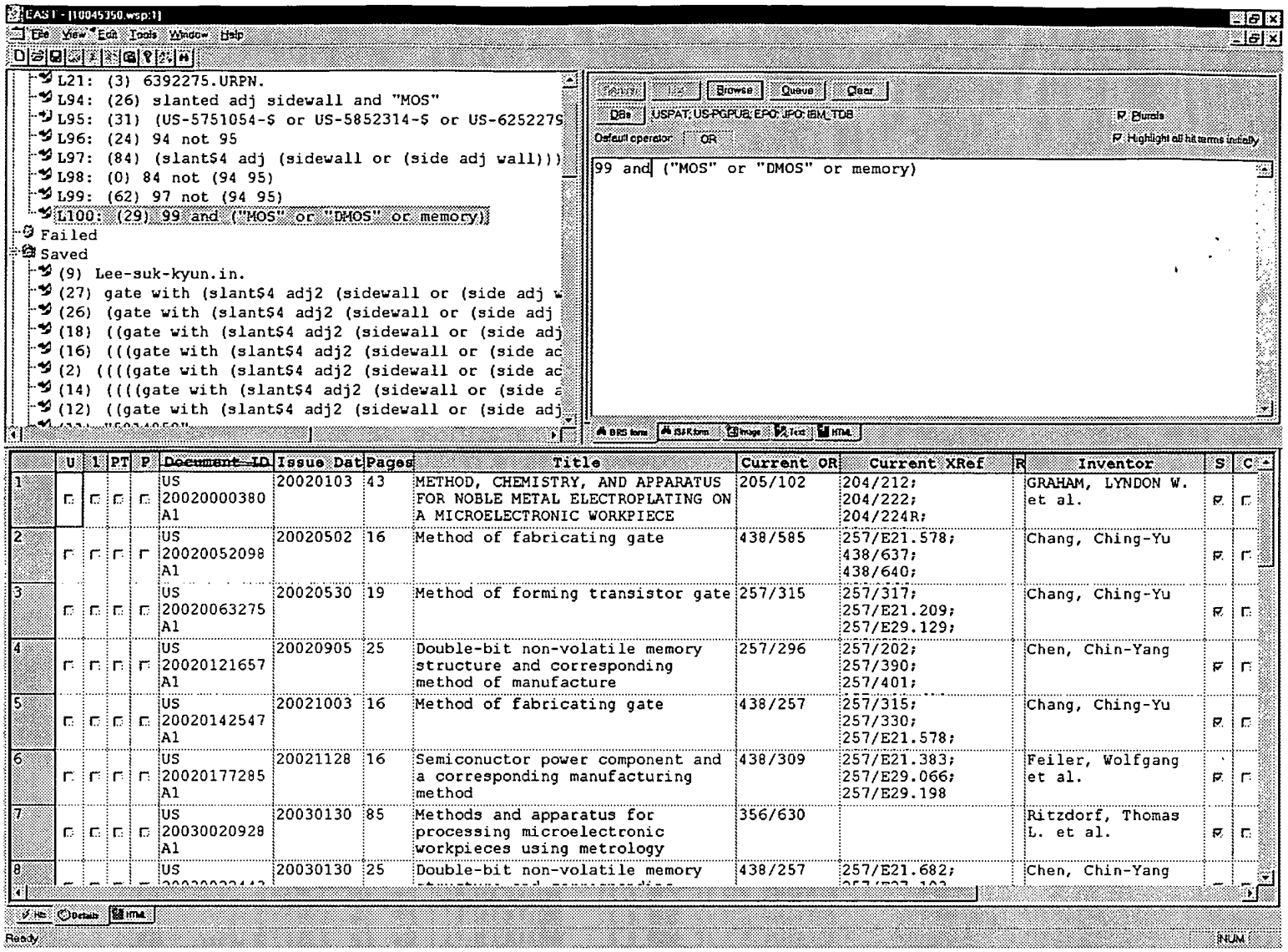

	U	1	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XRef	R	Inventor	S	C
1	☐	☐	☐	☐	US 20020000380 A1	20020103	43	METHOD, CHEMISTRY, AND APPARATUS FOR NOBLE METAL ELECTROPLATING ON A MICROELECTRONIC WORKPIECE	205/102	204/212; 204/222; 204/224R;		GRAHAM, LYNDON W. et al.	☑	☐
2	☐	☐	☐	☐	US 20020052098 A1	20020502	16	Method of fabricating gate	438/585	257/E21.578; 438/637; 438/640;		Chang, Ching-Yu	☑	☐
3	☐	☐	☐	☐	US 20020063275 A1	20020530	19	Method of forming transistor gate	257/315	257/317; 257/E21.209; 257/E29.129;		Chang, Ching-Yu	☑	☐
4	☐	☐	☐	☐	US 20020121657 A1	20020905	25	Double-bit non-volatile memory structure and corresponding method of manufacture	257/296	257/202; 257/390; 257/401;		Chen, Chin-Yang	☑	☐
5	☐	☐	☐	☐	US 20020142547 A1	20021003	16	Method of fabricating gate	438/257	257/315; 257/330; 257/E21.578;		Chang, Ching-Yu	☑	☐
6	☐	☐	☐	☐	US 20020177285 A1	20021128	16	Semiconuctor power component and a corresponding manufacturing method	438/309	257/E21.383; 257/E29.066; 257/E29.198		Feiler, Wolfgang et al.	☑	☐
7	☐	☐	☐	☐	US 20030020928 A1	20030130	85	Methods and apparatus for processing microelectronic workpieces using metrology	356/630			Ritzdorf, Thomas L. et al.	☑	☐
8	☐	☐	☐	☐	US [illegible]	20030130	25	Double-bit non-volatile memory [illegible]	438/257	257/E21.682; [illegible]		Chen, Chin-Yang		